

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claims 1-10 (canceled).

Claim 11 (currently amended): A method for removing a deposited film ~~inside a from a member located in a vacuum apparatus, said vacuum apparatus having a chamber which comprises said method comprising:~~

providing a hot element in the chamber, said hot element disposed away from the deposited film, the hot element having at least a surface which comprises platinum;

placing a said member, in said chamber;

exhausting said chamber;

heating the hot element to 400°C. or higher without generating a plasma;

supplying into the chamber a cleaning gas containing at least one of a fluorine atom and a chlorine atom;

contacting the cleaning gas with the heated hot element to decompose and/or activate the cleaning gas and generate an activated species therefrom;

allowing the activated species to convert the deposited film into a gaseous substance; and removing the gaseous substance from the chamber.

Claim 12 (previously presented): The method according to claim 11, wherein said chamber comprises a CVD apparatus and the method further comprises:

heating the hot element;

supplying a material gas to the chamber;

contacting the material gas with the hot element to cause decomposition and/or activation of the material gas by said hot element; and

forming the deposited film which comprises at least one element from said material gas on a substrate.

Claim 13 (previously presented): The method according to claim 11, wherein at least a part of a surface of an inner structure of said chamber is covered with platinum.

Claim 14 (previously presented): The method according to claim 12, wherein at least a part of the surface of an inner structure of said chamber is covered with platinum.

Claim 15 (previously presented): The method according to claim 11, wherein said cleaning gas is a gas containing at least one of fluorine ( $F_2$ ), chlorine ( $Cl_2$ ), nitrogen trifluoride ( $NF_3$ ), carbon tetrafluoride ( $CF_4$ ), hexafluoroethane ( $C_2F_6$ ), octafluoropropane ( $C_3F_8$ ), carbon tetrachloride ( $CCl_4$ ), pentafluorochloroethane ( $C_2ClF_5$ ), trifluorochlorine ( $ClF_3$ ), trifluorochloromethane ( $CClF_3$ ), and sulfur hexafluoride ( $SF_6$ ), and mixtures thereof.

Claim 16 (previously presented): The method according to claim 12, wherein said cleaning gas is a gas containing at least one of fluorine ( $F_2$ ), chlorine ( $Cl_2$ ), nitrogen trifluoride ( $NF_3$ ), carbon tetrafluoride ( $CF_4$ ), hexafluoroethane ( $C_2F_6$ ), octafluoropropane ( $C_3F_8$ ), carbon tetrachloride ( $CCl_4$ ), pentafluorochloroethane ( $C_2ClF_5$ ), trifluorochlorine ( $ClF_3$ ), trifluorochloromethane ( $CClF_3$ ), sulfur hexafluoride ( $SF_6$ ), and mixtures thereof.

Claims 17-26 (canceled).

Claim 27 (currently amended): A method for removing a deposited film from a wall inside a chamber, said method comprising:

providing a hot element, said hot element disposed away from said wall and said deposited film, said hot element having at least a surface which is composed of platinum;

heating said hot element to 400° C. or higher without generating a plasma;

supplying said chamber with a cleaning gas containing at least one of a fluorine atom and a chlorine atom, and first contacting said hot element with said gas to thereby activate said gas;

thereafter contacting the deposited film with said activated cleaning gas and converting said deposited film into a gaseous substance; and

removing said gaseous substance from said chamber.

Claim 28 (previously presented): The method according to claim 27, wherein said chamber comprises a CVD apparatus and the method further comprises:

- heating the hot element;
- supplying a material gas to the chamber;
- contacting the material gas with the hot element to cause decomposition and/or activation of the material gas by said hot element; and
- forming the deposited film which comprises at least one element from said material gas on a substrate.

Claim 29 (previously presented): The method according to claim 27, wherein at least a part of a surface of an inner structure of said chamber is covered with platinum.

Claim 30 (previously presented): The method according to claim 28, wherein at least a part of the surface of an inner structure of said chamber is covered with platinum.

Claim 31 (previously presented): The method according to claim 27, wherein said cleaning gas is a gas containing at least one of fluorine ( $F_2$ ), chlorine ( $Cl_2$ ), nitrogen trifluoride ( $NF_3$ ), carbon tetrafluoride ( $CF_4$ ), hexafluoroethane ( $C_2F_6$ ), octafluoropropane ( $C_3F_8$ ), carbon tetrachloride ( $CCl_4$ ), pentafluorochloroethane ( $C_2ClF_5$ ), trifluorochlorine ( $ClF_3$ ), trifluorochloromethane ( $CClF_3$ ), and sulfur hexafluoride ( $SF_6$ ), and mixtures thereof.

Claim 32 (previously presented): The method according to claim 28, wherein said cleaning gas is a gas containing at least one of fluorine ( $F_2$ ), chlorine ( $Cl_2$ ), nitrogen trifluoride ( $NF_3$ ), carbon tetrafluoride ( $CF_4$ ), hexafluoroethane ( $C_2F_6$ ), octafluoropropane ( $C_3F_8$ ), carbon tetrachloride ( $CCl_4$ ), pentafluorochloroethane ( $C_2ClF_5$ ), trifluorochlorine ( $ClF_3$ ), trifluorochloromethane ( $CClF_3$ ), sulfur hexafluoride ( $SF_6$ ), and mixtures thereof.

Claim 33 (new): The method according to claim 11, wherein said member is at least one of a measurement instrument, a sensor, a valve, and a pipe.